One Watt High Voltage Transistor

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	300	Vdc
Collector – Base Voltage	V _{CBO}	300	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ι _C	500	mAdc
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	PD	1.0 8.0	W mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	2.5 20	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

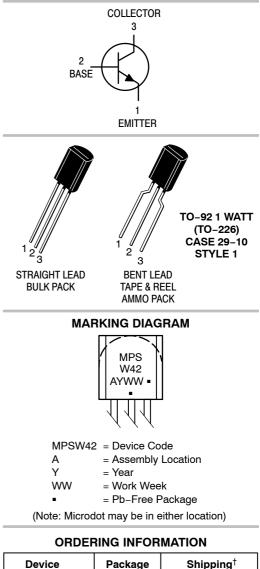
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

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Device	Гаскаде	ompping
MPSW42	TO-92	5000 Units/Box
MPSW42G	TO–92 (Pb–Free)	5000 Units/Box
MPSW42RLRA	TO-92	2000/Tape & Reel
MPSW42RLRAG	TO-92 (Pb-Free)	2000/Tape & Reel

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MPSW42

ELECTRICAL CHARACTERISTICS (T_A = 25° C unless otherwise noted)

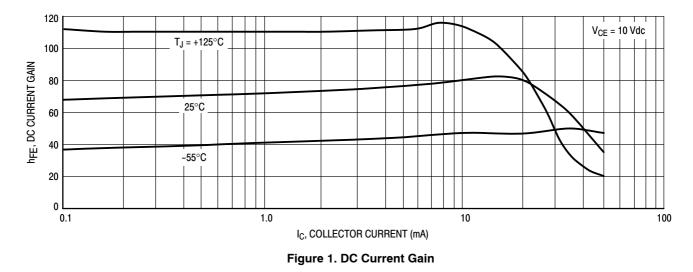
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•	•	
Collector – Emitter Breakdown Voltage (Note 1) ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	300	_	Vdc
Collector-Base Breakdown Voltage $(I_{C} = 100 \ \mu Adc, I_{E} = 0)$	V _{(BR)CBO}	300	-	Vdc
Emitter–Base Breakdown Voltage (I _E = 100 μAdc, I _C = 0)	V _{(BR)EBO}	6.0	-	Vdc
Collector Cutoff Current (V _{CB} = 200 Vdc, I _E = 0)	Ісво	-	0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 6.0 \text{ Vdc}, I_C = 0$)	I _{EBO}	-	0.1	μAdc
ON CHARACTERISTICS				
$ \begin{array}{l} \text{DC Current Gain} \\ (I_{C} = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) \\ (I_{C} = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) \\ (I_{C} = 30 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) \end{array} $	h _{FE}	25 40 40		-
Collector-Emitter Saturation Voltage (I _C = 20 mAdc, I _B = 2.0 mAdc)	V _{CE(sat)}	-	0.5	Vdc
Base-Emitter Saturation Voltage (I _C = 20 mAdc, I _B = 2.0 mAdc)	V _{BE(sat)}	-	0.9	Vdc

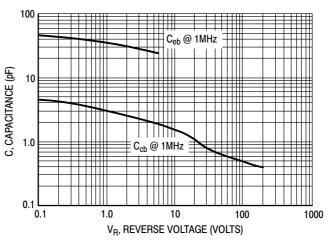
SMALL-SIGNAL CHARACTERISTICS

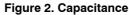
Current–Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 20 MHz)	f _T	50	_	MHz
Collector Capacitance $(V_{CB} = 20 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{cb}	1	3.0	pF

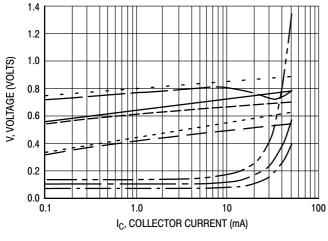
1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

MPSW42

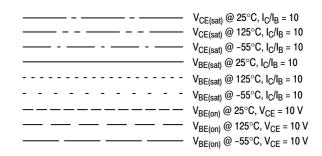




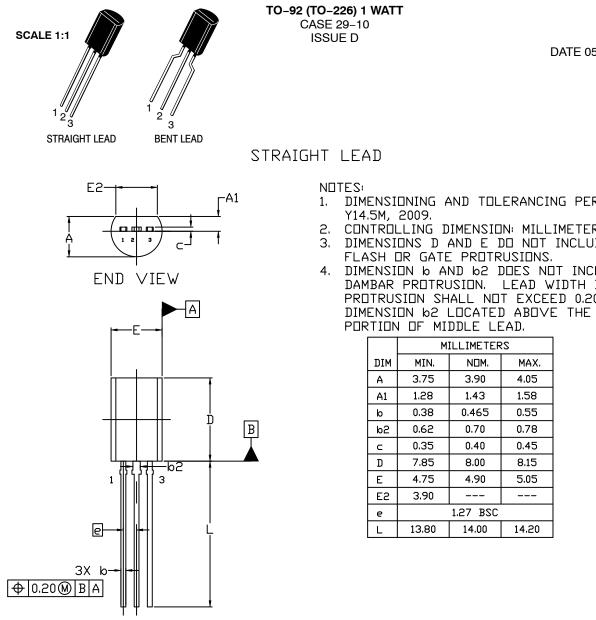








semi



TOP VIEW

- DIMENSIONING AND TOLERANCING PER ASME
- CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR

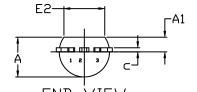
STYLES AND MARKING ON PAGE 3

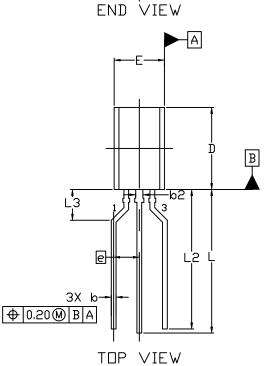
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DESCRIPTION: TO-92 (TO-226) 1 WATT PAGE 1 OF :		PAGE 1 OF 3	
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DATE 05 MAR 2021

DATE 05 MAR 2021

FORMED LEAD





NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION b AND b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION b2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	М	ILLIMETER	22
DIM	MIN.	NDM.	MAX.
Α	3.75	3.90	4.05
A1	1.28	1.43	1.58
α	0.38	0.465	0.55
b2	0.62	0.70	0.78
с	0.35	0.40	0.45
D	7.85	8.00	8.15
E	4.75	4.90	5.05
E5	3.90		
e		2.50 BSC	
L	13.80	14.00	14.20
L2	13.20	13.60	14.00
L3		3.00 REF	

STYLES AND MARKING ON PAGE 3

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DATE 05 MAR 2021

STYLE 5:

2.	EMITTER BASE COLLECTOR
2.	GATE SOURCE & SUBSTRATE DRAIN
2.	ANODE CATHODE & ANODE CATHODE
2.	ANODE GATE CATHODE
2.	COLLECTOR EMITTER BASE
STYLE 26 PIN 1. 2. 3.	V _{CC}
2.	GATE DRAIN SOURCE

	BASE EMITTER COLLECTOR
2.	SOURCE DRAIN GATE
2	MAIN TERMINAL 1 GATE MAIN TERMINAL 2
2.	COLLECTOR BASE EMITTER
2.	SOURCE GATE DRAIN

2.	ANODE ANODE CATHODE
2.	DRAIN GATE SOURCE & SUBSTRATE
2.	ANODE 1 GATE CATHODE 2
2.	ANODE CATHODE NOT CONNECTED
	GATE SOURCE DRAIN
2.	CATHODE ANODE GATE
2.	RETURN INPUT OUTPUT

2.	CATHODE CATHODE ANODE
2.	BASE 1 EMITTER BASE 2
2.	EMITTER COLLECTOR BASE
2.	EMITTER Collector/Anode Cathode
2.	NOT CONNECTED ANODE CATHODE
STYLE 34: PIN 1.	INPUT

2. GROUN 3. LOGIC GROUND

PIN 1. DRAIN SOURCE 2. 3. GATE STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2 STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

GENERIC **MARKING DIAGRAM***

XXXXX XXXXX ALYW= .

XXXX = Specific Device Code

- А = Assembly Location
- L = Wafer Lot
- Υ = Year
- W = Work Week
 - = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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